Thyristor Semiconductor Device - Page 1 of 1



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| Inclosure Material: |
|---|
| Metal |
| Overall Length: |
| 2.637 inches |
| Overall Diameter: |
| 1.031 inches |
| Mounting Facility Quantity: |
| 1 |
| Joint Electronic Device Engineering Council/jedec/case Outline Designation: |
| То-83 |
| Electrode Internally-electrically Connected To Case: |
| Anode |
| Mounting Method: |
| Threaded stud |
| Overall Width Across Flats: |
| Between 1.031 inches and 1.063 inches |
| Thread Size: |
| 0.500 inches |
| Semiconductor Material: |
| Silicon |
| Voltage Rating In Volts Per Characteristic: |
| 1500.0 repetitive peak reverse voltage and 1800.0 nonrepetitive peak reverse voltage |
| Current Rating Per Characteristic: |
| 10.00 milliamperes forward current, total rms and 10.00 milliamperes forward current, average nanoamperes |
| Power Rating Per Characteristic: |
| 16.0 watts small-signal input power, common-collector blank |
| Maximum Operating Tempurature Per Measurement Point: |
| 125.0 degrees celsius junction |
| Thread Series Designator: |
| Unf |
| Terminal Type And Quantity: |
| 2 tab, solder lug and 1 threaded stud |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| No |
| Fiig: |
| A110a0 |
| Fiig: |